



THIS SHEET HAS BEEN
REPLACED

Abstract

Disclosed is a semiconductor device having complementary metal insulator semiconductor field-effect transistors (MISFETs) in which a plurality of basic cells having N-channel MOSs and P-channel MOSs are disposed. In this semiconductor device, a sub MISFET is disposed adjacently to a stopper layer in a region adjacent to other basic cell. An element such as a transmission gate composed of a single element can be actualized by use of the sub-MISFET. In the semiconductor device of this invention, a working efficiency thereof is improved. A response velocity of the P-channel MOS can also be improved using the sub-MISFET. A numerical quantity of the basic cells constituting a circuit can be reduced, resulting in a reduction in parasitic capacity. An operating time of the circuit is thereby decreased.